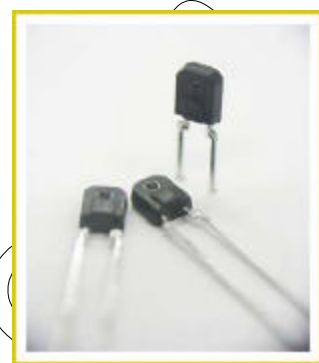


Phototransistor KDT2001

Description

- The KDT2001 is a high-sensitivity NPN silicon phototransistor.
- Visible ray cut-off mold type
 - : Spectral sensitivity : $\lambda = 700\sim 1050\text{nm}$
 - : Peak sensitivity wavelength : $\lambda P = 860\text{nm}$
- High reliability, Low power dissipation and Long life span.
- It's free from Environmental hazardous substances (Pb, Hg, Cd, Cr+6, PBB, PBDE).
- It is designed for use in general electric equipments such as OA, Household appliances, etc.



Features

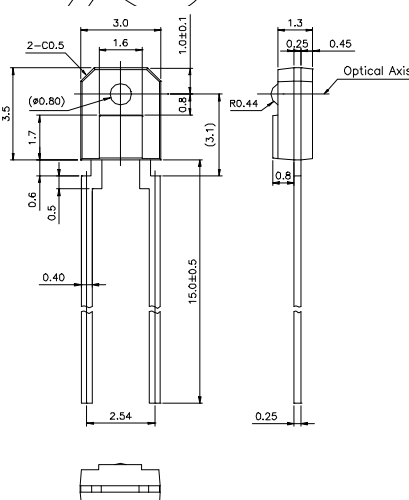
- Visible ray cut-off mold type
- Single phototransistor output
- Compact ($t=1.5\text{mm}$)
- Half angle : $\pm 40^\circ$



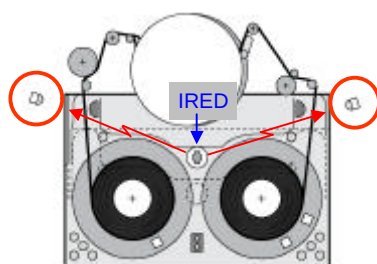
Application

- Optical switches
- Video camera
- Floppy disk drive
- Tape end sensor

Outline Dimensions



** Tape end sensor



Characteristics

[$T_a = 25^\circ\text{C}$]

Parameter	Symbol	Ratings	Unit
Collector-Emitter breakdown voltage	BV_{CEO}	35	V
Emitter-Collector breakdown voltage	BV_{ECO}	6	V

Parameter	Symbol	Characteristics	Unit
Light current. ($E_e=1\text{mW/cm}^2$, $V_{CE}=5\text{V}$)	I_{CEL}	0.25(TYP.)	mA
Collector dark current ($E_e=0$, $V_{CE}=10\text{V}$)	I_{CEO}	100(MAX.)	nA
Peak wavelength	λ_P	860	nm